

Description

The ASLXX is a low capacitance TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The ASLXX complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to high speed interfaces and transmission lines from voltage surges.

Features

- 300W peak pulse power (8/20µs)
- Two devices protect one line
- Ultra low leakage: nA level
- Operating voltage: 5V, 12V, 24V, 36V
- Low capacitance for high-speed data line
- Low clamping voltage
- Complies with following standards:
 IFC 61000 4.2 (FSD) immunity to
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±30kV
 Contact discharge: ±30kV
- RoHS Compliant

Mechanical Characteristics

- Package: SOT-23
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Notebooks and Handhelds
- Portable Instrumentation
- Set Top Box
- Industrial Controls
- Server and Desktop PC
- High-Speed data line
- LAN/WAN equipment

Marking Information

 LXX = Device Marking

 3
 Part Number
 Marking

 ASL05
 L05

 ASL12
 L12

 ASL24
 L24

 ASL36
 L36

Dimensions and Pin Configuration





Circuit Diagram

Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
ASL05	3000/Tape & Reel	7 inch
ASL12	3000/Tape & Reel	7 inch
ASL24	3000/Tape & Reel	7 inch
ASL36	3000/Tape & Reel	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	300	W
ESD per IEC 61000-4-2 (Air)	Vrop		k\/
ESD per IEC 61000-4-2 (Contact)	VESD	±30	κv
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

ASL05						
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	Vbr	6			V	IT = 1mA
Reverse Leakage Current	I _R			0.5	μA	VRWM = 5V
Clamping Voltage	Vc			9.8	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			11	V	IPP = 5A (8 x 20µs pulse)
Peak Pulse Current	IPP			17	А	t _p = 8/20µs
Junction Capacitance	CJ			5	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 2



ASL12							
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition	
Reverse Working Voltage	VRWM			12	V		
Breakdown Voltage	Vbr	13.3			V	IT = 1mA	
Reverse Leakage Current	I _R			0.5	μA	VRWM = 12V	
Clamping Voltage	Vc			19	V	IPP = 1A (8 x 20µs pulse)	
Clamping Voltage	Vc			24	V	IPP = 5A (8 x 20µs pulse)	
Peak Pulse Current	IPP			12	Α	t _p = 8/20µs	
Junction Capacitance	СЈ			5	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 2	

ASL24						
Parameter	Symbol	Min	Тур	Мах	Unit	Test Condition
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	VBR	27			V	IT = 1mA
Reverse Leakage Current	I _R			0.5	μA	VRWM = 24V
Clamping Voltage	Vc			40	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			60	V	IPP = 5A (8 x 20µs pulse)
Peak Pulse Current	IPP			5	А	t _p = 8/20µs
Junction Capacitance	Сл			5	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 2

ASL36						
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			36	V	
Breakdown Voltage	VBR	38			V	IT = 1mA
Reverse Leakage Current	I _R			0.5	μA	VRWM = 36V
Clamping Voltage	Vc			50	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			75	V	IPP = 4A (8 x 20µs pulse)
Peak Pulse Current	IPP			4	А	t _p = 8/20µs
Junction Capacitance	Сл			5	pF	VR = 0V, f = 1MHz, Pin 1 to Pin 2





Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

Peak Pulse Power vs. Pulse Time





8 X 20µs Pulse Waveform



Device Connection for Protection of One High-Speed Data Line

The ASL series devices are designed to protect high speed data lines. The ASLXX utilizes a low capacitance compensa tion diode in series with, but in opposite polarity to a TVS diode in each line to achieve an effective capacitance of less than 5pF per device. During a transient event, the internal rectifier must be forward biased (TVS is reversed biased). Therefore, each device will only suppress transient events in one polarity. To achieve protection in both positive and negative polarity, a second device is connected in anti-parallel to the first.



Two Devices : Bidirectional or Unidirectional Line



I/O Line Protection



SOT-23 Package Outline Drawing



	DIMENSIONS								
	Ν	MILLIMETER	S	INCHES					
SYM	MIN	NOM	MAX	MIN	NOM	MAX			
A	0.90		1.15	0.035		0.045			
A1	0.00		0.10	0.000		0.004			
A2	0.90		1.05	0.035		0.041			
b	0.30		0.50	0.012		0.020			
с	0.08		0.15	0.003		0.006			
D	2.80		3.00	0.110		0.118			
E	1.20		1.40	0.047		0.055			
E1	2.25		2.55	0.089		0.100			
е		0.95TYP			0.037TYP				
e1	1.80		2.00	0.071		0.079			
L		0.55REF			0.022REF				
L1	0.30		0.50	0.012		0.020			
Θ	0°		8°	0°		8°			



ASL05 through ASL36

Suggested Land Pattern



evm	DIMENSIONS						
5111	INCHES	MILLIMETERS					
С	(.087)	(2.20)					
E	.037	0.95					
E1	.075	1.90					
G	.031	0.80					
Х	.039	1.00					
Y	.055	1.40					
Z	.141	3.60					

Contact Information

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日期	版本号	描述	页码
2018.11.05	1.0	原版	
2019.01.08	2.0	更改了原理图, PIN 3从NC变为有电气连接	1, 5